

**CMLD6263**  
**SURFACE MOUNT**  
**PICOmini™**  
**DUAL, ISOLATED**  
**HIGH VOLTAGE**  
**SILICON SCHOTTKY DIODES**



# Central™

## Semiconductor Corp.

**FEATURES:**

- HIGH VOLTAGE (70V)
- LOW FORWARD VOLTAGE
- GALVANICALLY ISOLATED

**DESCRIPTION:**

The Central Semiconductor CMLD6263 incorporates two galvanically isolated, High Voltage, low  $V_F$  Silicon Diodes in a space saving SOT-563 surface mount package. These diodes are designed for fast switching applications requiring a low forward voltage drop.

**MARKING CODE: 63D**

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

Peak Repetitive Reverse Voltage  
 Continuous Forward Current  
 Forward Surge Current,  $t_p=1.0$  s  
 Power Dissipation  
 Operating and Storage  
 Junction Temperature  
 Thermal Resistance

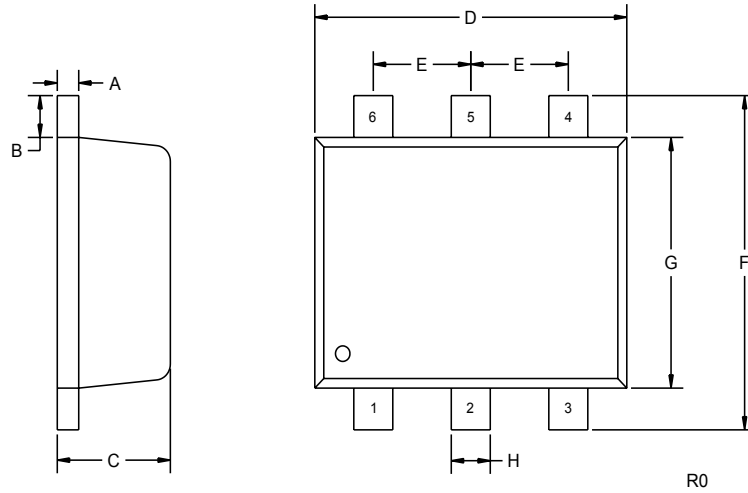
SYMBOL		UNITS
$V_{RRM}$	70	V
$I_F$	15	mA
$I_{FSM}$	50	mA
$P_D$	250	mW
$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
$\theta_{JA}$	500	$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS PER DIODE:** ( $T_A=25^\circ\text{C}$ )

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
$I_R$	$V_R=50\text{V}$		98	200	nA
$BV_R$	$I_R=10\mu\text{A}$	70			V
$V_F$	$I_F=1.0\text{mA}$		395	410	mV
$C_T$	$V_R=0\text{V}, f=1.0\text{MHz}$			2.0	pF
$t_{rr}$	$I_R=I_F=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$			5.0	ns

R1 ( 20-February 2003)

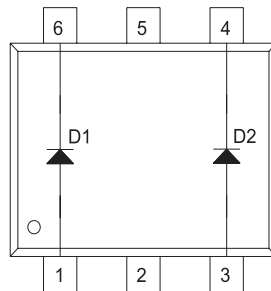
**SOT-563 CASE - MECHANICAL OUTLINE**



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.007	0.10	0.18
B	0.008		0.20	
C	0.022	0.024	0.56	0.60
D	0.059	0.067	1.50	1.70
E	0.020		0.50	
F	0.061	0.067	1.55	1.70
G	0.047		1.20	
H	0.006	0.012	0.15	0.30

SOT-563 (REV: R0)

**Pin Configuration**



**LEAD CODE:**

- 1) ANODE D1
- 2) NC
- 3) ANODE D2
- 4) CATHODE D2
- 5) NC
- 6) CATHODE D1

**MARKING CODE: 63D**